

TCU12UYG-H



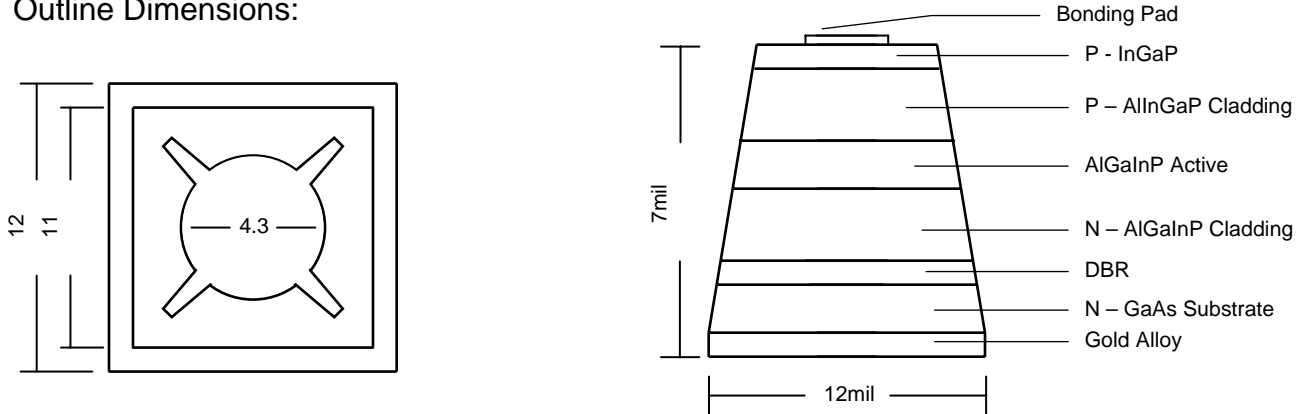
❖ Features:

- AllInGaP/GaAs LED Chips
- MOVPE Process Wafer
- MQW and DBR
- Roughen Surface

❖ Typical Applications

- Indoor/Outdoor Applications

❖ Outline Dimensions:



❖ Physical Structure:

Chip dimensions		Chip size	12 mil x 16 mil	305 μ m x 305 μ m
		Thickness	11 mil	279 μ m
		Emission area	11 mil	279 μ m
		Bonding pad	4.3 mil	109 μ m
Electrode	Top	P (anode)	Gold alloy	
	Backside	N (cathode)	Gold alloy	

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$		2.00	2.40	V
Wavelength	λ_D	$I_F = 20\text{mA}$	577	580	583	
Spectral width at half height	$\Delta\lambda$	$I_F = 20\text{mA}$	-	15	-	nm
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Luminous Intensity	I_v	C	35	-	-	mcd
		D	50	-	-	

YELLOW